

## ABSTRACT

A method for fabricating a semiconductor device comprising at least one component having photolithographic proximity-limited geometries (702). The method comprises the steps of dividing the component into a plurality of sub-geometries (703), wherein each of these sub-geometries contains only structural elements spaced far enough to be compatible with photomask rules. A separate photomask (704) is then made for each of the sub-geometries. Each of these photomasks is sequentially used in a plurality of photoresist printing steps (705) so that the semiconductor device component is created step by step.